

### IN THE CLAIMS

Please amend the claims as follows.

1. - 31. (Canceled)

32. (Currently Amended) A method comprising:

forming a via in a substrate;

removing a portion of the via in the substrate to form a first via portion and a second via portion; and

forming an electrical component in the via in the substrate, ~~wherein the electrical component includes at least a portion of memory.~~

33. (Previously Presented) The method of claim 32 wherein forming an electrical component in the via includes forming at least a portion of a resistor.

34. (Previously Presented) The method of claim 32 wherein forming an electrical component in the via includes forming at least a portion of a capacitor.

35. (Previously Presented) The method of claim 32 wherein forming an electrical component in the via includes forming at least a portion of a core.

36. (Previously Presented) The method of claim 32 wherein forming an electrical component in the via includes forming a resistor.

37. (Previously Presented) The method of claim 32 wherein forming an electrical component in the via includes forming a core.

38. (Canceled)

39. (Previously Presented) The method of claim 32 wherein forming an electrical component in the via includes forming a memory.

40. (Previously Presented) The method of claim 32 wherein the electrical component in the via includes a passive electrical component.

41. (Previously Presented) The method of claim 32 wherein the electrical component in the via is a passive electrical component.

42. (Previously Presented) The method of claim 32 wherein the electrical component includes a capacitor further comprising:

- an inner cylindrical portion; and
- an outer via portion substantially surrounding the inner cylindrical portion.

43. (Previously Presented) The method of claim 32 wherein the electrical component includes a capacitor further comprising:

- a first curved portion; and
- a second curved portion spaced from the first curved portion, wherein the distance between the first curved portion and the second curved portion vary.

44. (Previously Presented) The method of claim 32 wherein the electrical component includes a capacitor further comprising:

- a first curved portion; and
- a second curved portion spaced from the first curved portion, wherein the first curved portion and the second curved portion are portions of a via formed by insulating a first portion of a via from a second portion of a via.

45. (Previously Presented) A method comprising:

- forming a via in a substrate; and
- forming at least a portion of a transformer within the via.

46. - 68. (Canceled)

69. (Previously Presented) A method comprising:

forming a via in a substrate; and

forming a capacitor in the via in the substrate, wherein forming the capacitor further comprises:

forming a first curved plate portion; and

forming a second curved plate portion spaced from the first curved plate portion, wherein the distance between the first curved plate portion and the second curved plate portion vary.

70. (Previously Presented) A method comprising:

forming a via in a substrate; and

forming a capacitor in the via in the substrate, wherein forming the capacitor further comprises:

forming a first curved plate portion; and

forming a second curved plate portion spaced from the first curved plate portion, wherein the first curved plate portion and the second curved plate portion are portions of a via formed by insulating the first portion of a via from a second portion of a via.

71. (Canceled)

72. (New) The method of claim 32 wherein forming an electrical component in the via further includes:

forming a first electrical component from the first via portion; and

forming a second electrical component from the second via portion.

**AMENDMENT UNDER 37 C.F.R. 1.116 – EXPEDITED PROCEDURE**

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Assignee: Intel Corporation

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73. (New) The method of claim 32 wherein removing a portion of the via in the substrate to form a first via portion and a second via portion further includes:

masking a portion of the via; and

etching an unmasked portion of the via.